



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- $BV_{CEO} > 300V$
- $I_C = 3.5A$ High Continuous Collector Current
- $I_{CM} = 5A$ Peak Pulse Current
- Very Low Saturation Voltage $V_{CE(SAT)} < 155mV @ 1A$
- $R_{CE(SAT)} = 87m\Omega$ for a Low Equivalent On-Resistance
- h_{FE} Specified Up to 3A for a High Gain Hold-Up
- Complementary PNP Type: NK-FZT957

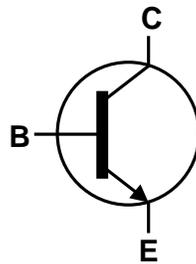
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ^(e3)
- Weight: 0.112 grams (Approximate)

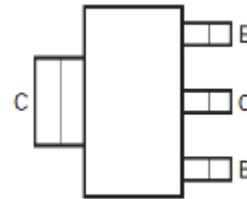
SOT223



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings

 (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	350	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	3.5	A
Peak Pulse Current	I_{CM}	5	A

Thermal Characteristics

 (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P_D	3.0	W mW/ $^{\circ}\text{C}$
		24	
		1.6 12.8	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	42	$^{\circ}\text{C}/\text{W}$
	$R_{\theta JA}$	78	
Thermal Resistance Junction to Lead	$R_{\theta JL}$	8.8	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^{\circ}\text{C}$

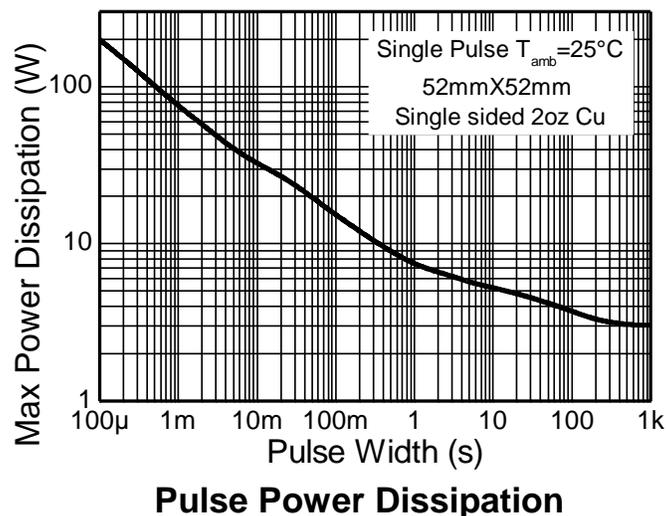
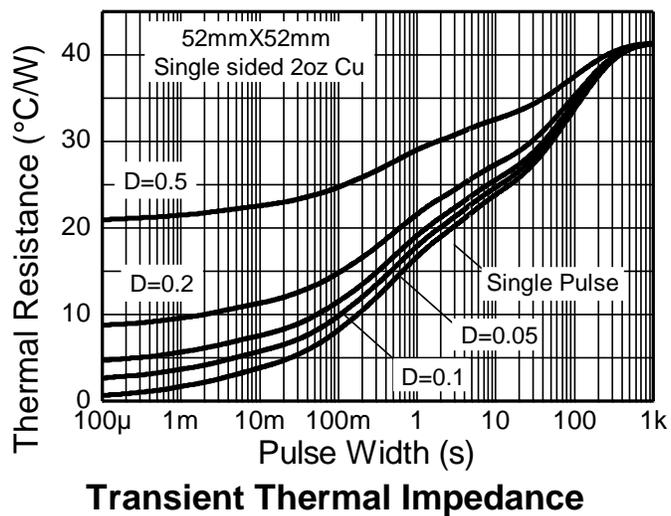
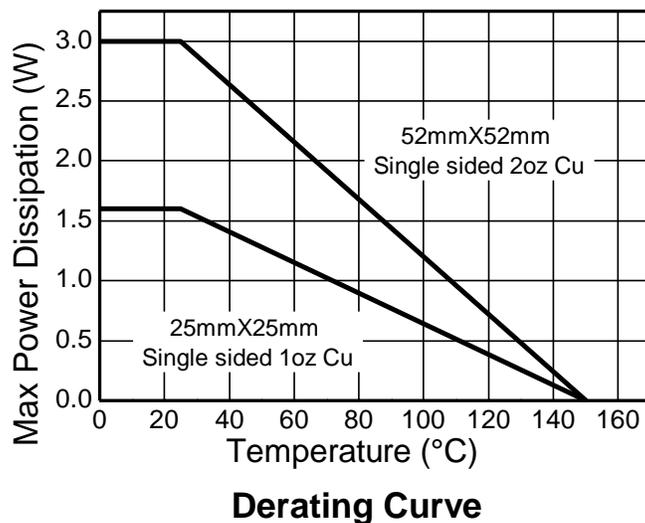
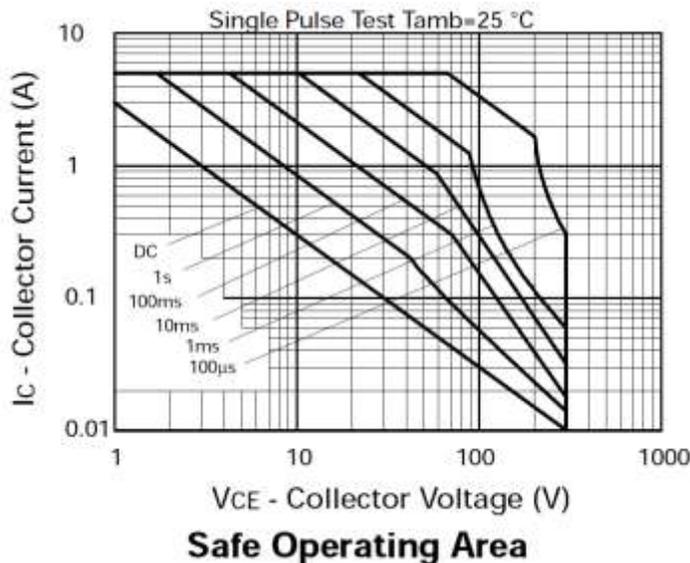
ESD Ratings

 (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
 7. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

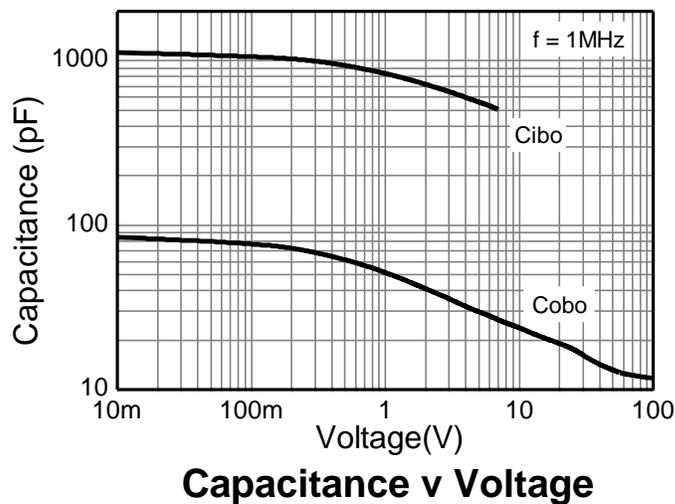
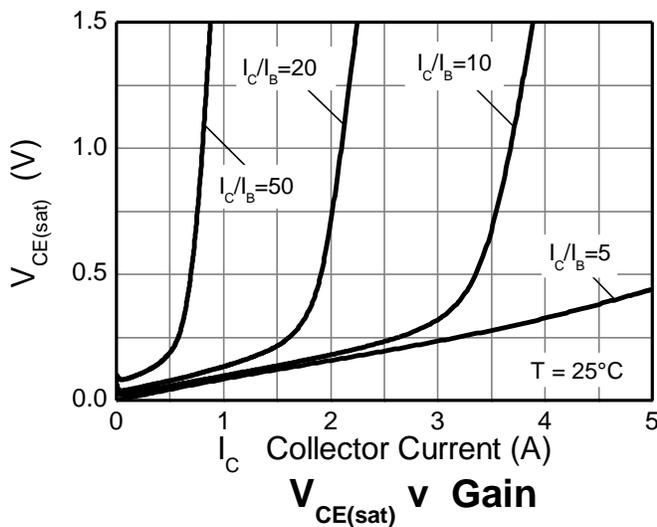
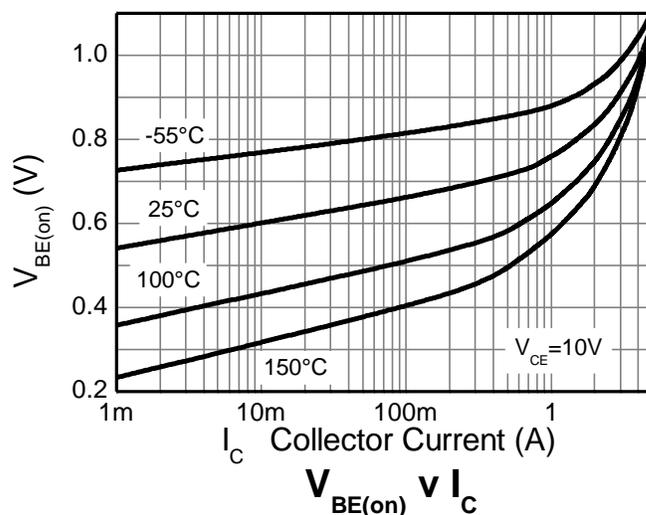
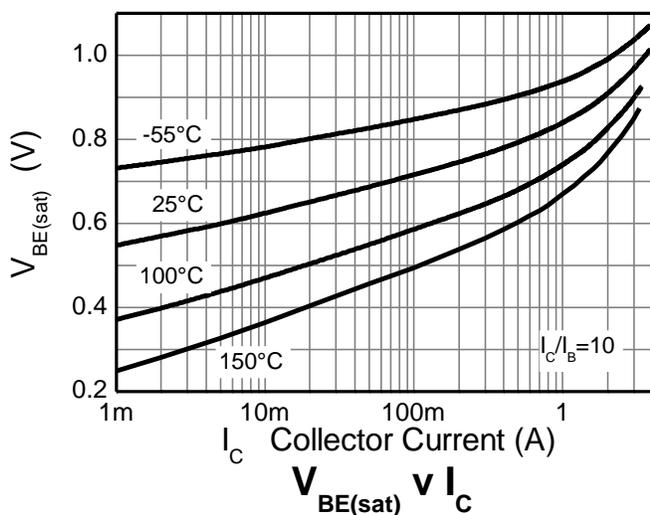
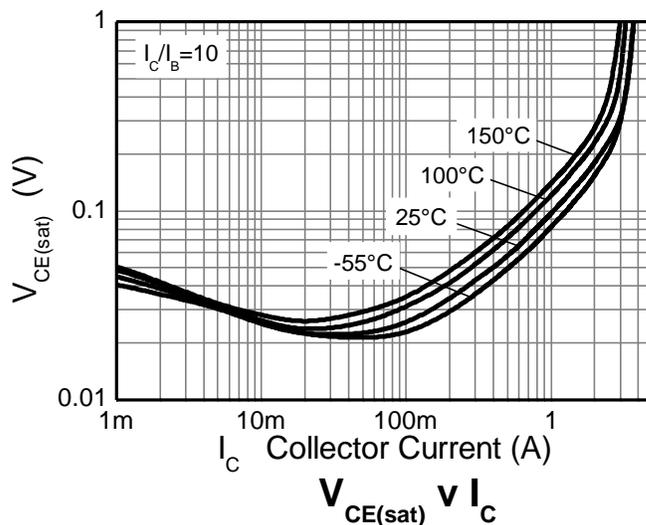
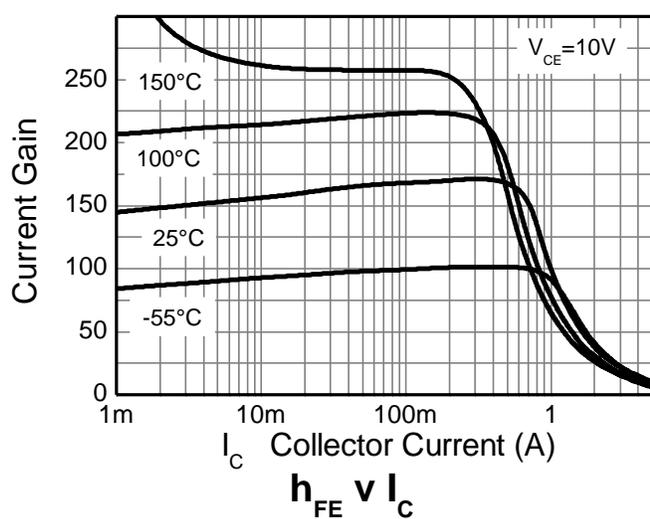


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	350	475	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV _{CER}	350	475	—	V	I _C = 1μA, R _B ≤ 1kΩ
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	300	350	—	V	I _C = 1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8	—	V	I _E = 100μA
Collector Cut-Off Current	I _{CBO}	—	<1	50	nA μA	V _{CB} = 300V V _{CB} = 300V, T _A = +100°C
Collector Cut-Off Current	I _{CER}	—	<1	50	nA μA	V _{CE} = 300V, R _B ≤ 1kΩ V _{CE} = 300V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	—	<1	10	nA	V _{EB} = 6V
DC Current Gain (Note 10)	h _{FE}	100	200	—	—	I _C = 10mA, V _{CE} = 5V
		100	200	300		I _C = 500mA, V _{CE} = 10V
		15	25	—		I _C = 2A, V _{CE} = 10V
		—	15	—		I _C = 3A, V _{CE} = 10V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(SAT)}	—	59	100	mV	I _C = 500mA, I _B = 50mA
		—	95	155		I _C = 1A, I _B = 100mA
		—	180	230		I _C = 2A, I _B = 200mA
		—	300	345		I _C = 3.5A, I _B = 600mA
Base-Emitter Saturation Voltage (Note 10)	V _{BE(SAT)}	—	1,020	1,250	mV	I _C = 3.5A, I _B = 600mA
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(ON)}	—	940	1,120	mV	I _C = 3.5A, V _{CE} = 10V
Current Gain-Bandwidth Product (Note 10)	f _T	—	80	—	MHz	I _C = 100mA, V _{CE} = 10V, f = 50MHz
Output Capacitance	C _{OBO}	—	21	—	pF	V _{CB} = 20V, f = 1MHz
Switching Times	t _{ON}	—	100	—	ns	I _C = 250mA, V _{CC} = 50V, I _{B1} = -I _{B2} = 25mA
	t _{OFF}	—	5,300	—		

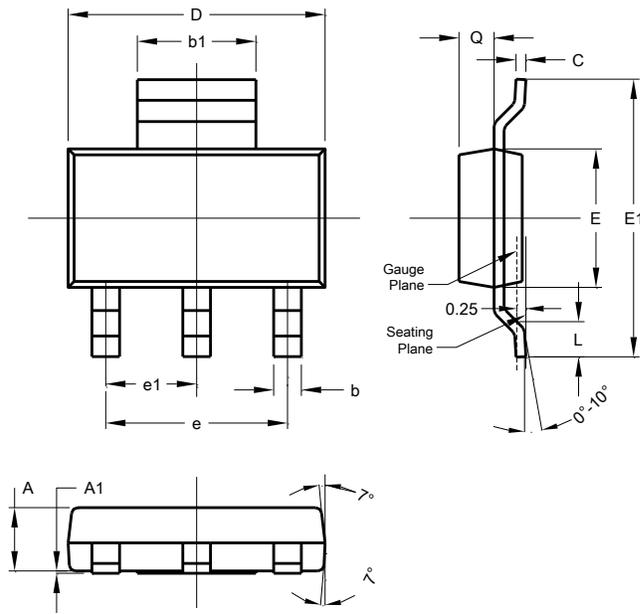
Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



Package Outline Dimensions

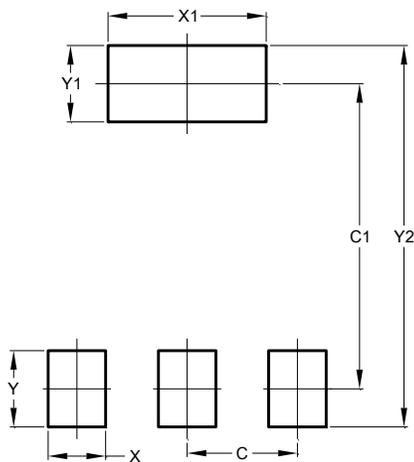
SOT223



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.